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| Objective |
| Batch name: |
| This process flows is a guideline on how to spin, develop and rinse AZ4562 on substrates as Si, SiO2 and SOI, using the SSE Spin coater. |

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| Step Heading | Equipment |  | Comments |
| 1. Pretreatment | | |  |
| * 1. Surface treatment | BHF dip  *or*  250C oven | BHF dip for Si substrates (30 sec, H2O 5 min)  Overnight bake | HMDS pretreatment can course bobbles in resist during exposure. |
| 1. Spin coat of AZ4562, 10µm | | |  |
| * 1. Clean spinner | SSE spinner | Clean spinner nozzle and run the dummy wafers  Recipe: AZ4562\_10um | 1-3 dummies |
| * 1. Coat wafers | SSE Spinner | **Resist:** AZ4562  **Recipe:** AZ4562\_10um  **Softbake:**  is included in the spinning recipe  300sec@100C | Resist thickness can be measured with FilmTek recipe: resist\_QC\_9points |
| In case you will have a thicker resist |  | With AZ4562 you can build up the thickness spinning more than one time. Use a lower temperature for softbake between the spinning  **Recipe:**….. |  |
| * 1. Coat wafers | SSE Spinner | **Repeat step 2.2** |  |
| 1. Exposure | | |  |
| * 1. Exposure | Aligner-6inch  KS Alignment | **Recipe:** DCH\_10um\_FPA in case you will not align  Or DCH\_10um\_TSA in case you do a Top Side Alignment  **Exposure mode:** Hard Contact  **Exposure time:** 20sec, to avoid resist overheating use interval exposure  **Mask**: your mask  **Exposure mode:** Hard Contact  **Exposure time:** 40 sec, to avoid resist overheating use multiple exposure  **Mask**: your mask | We suggest you do a dose test exposure to find an optimum exposure for your process.  Activate interval exposure with 10sec wait time between exposure  Activate multiple exposure with 10sec wait time between exposure |
| 1. Development & Rinse | | |  |
| * 1. Develop | Developer bench | Develop in 351B for 300±10 sec |  |
|  | Wet bench/ Spin dryer | Rinse in DI water for 5 min (300±30 sec).  Spin dry |  |
| 1. Inspection | | |  |
| * 1. Inspection | Optical microscope | Check pattern and alignment marks |  |